## Ultrasonic Treatment Effects on CuS<sub>1.8</sub> – CdSe Structures

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Ultrasound (US) is established to affect properties of II-VI semiconductors [1, 2]. However to the best of our knowledge, there have not reports on US influence on II-VI-based solar cells, whereas similar effects are detected in other barrier structures [3]. Our work has focuced on the modification by US treatment (UST) of electrical properties of CuS<sub>1.8</sub> – CdSe thin film photodetector. The longitudinal waves (8.4MHz) were used for UST. The current-voltage characteristics were measured over a temperature range 290-340 K both before and after UST.

The analysis has been shown that the recombination-tunnel current mechanism is realized under a forward bias and both trap-assisted tunneling and trap-charge limited current determine carrier transmission under a reverse bias. UST leads to decrease of the tunneling parameter ( $\alpha$ ), the saturation current ( $I_0$ ), the trap activation energy in the diod base ( $E_X$ ) as well as to increase of both the shunt ( $R_{SH}$ ) and the series ( $R_S$ ) resistance, the barrier height ( $V_d$ ), the energy level of traps, which are located in the space charge region. Some parameters are subjected to the complete ( $E_X$ ,  $E_S$ ,  $E_S$ ,  $E_S$ ,  $E_S$ ,  $E_S$ , activation energy) or partial ( $E_S$ ,  $E_S$ , value) recovery after the sample storage at room temperature. On our opinion, the observed effects deal with the acoustically induced defect generation.

<sup>[1]</sup> R. Savkina, A. Smirnov, and F. Sizov, Semicond. Sci. Technol. 22, 97 (2007).

<sup>[2]</sup> M. Sheinkman et al., Mat. Sci. Forum 196-201, 1467 (1995)

<sup>[3]</sup> O. Olikh, K. Voytenko, and R. Burbelo, J. Appl. Phys. **117**, 044505 (2015)

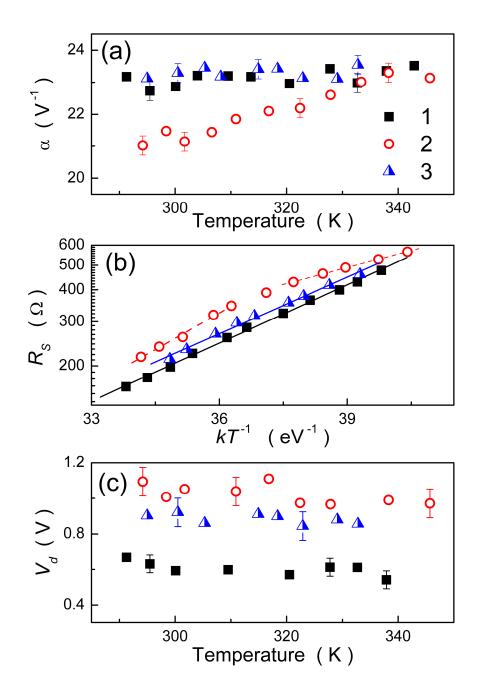


Figure. Temperature dependencies of tunneling parameter  $\alpha = d(\ln I)/dV$  (a), series resistance (b) and barrier height (c). The measurements were taken before UST (curves 1, squares), immediately after UST (curves 2, circles), and after UST and ~75 h room temperature storage (curves 3, triangles).